

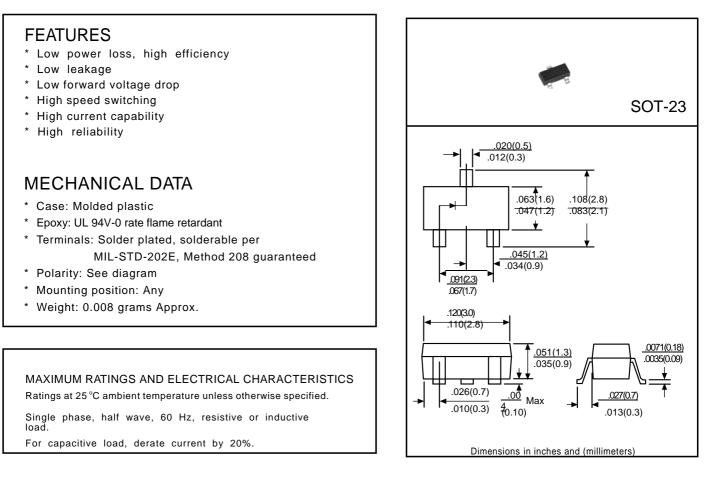
ENTERPRISE CORP. HITANO ENTERPRISE CORP.

MMBD4148, MMBD4448

TECHNICAL SPECIFICATIONS OF SURFACE MOUNT SWITCHING DIODES

VOLTAGE - 100 Volts

CURRENT - 0.15 Ampere

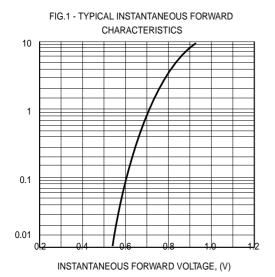


	SYMBOL	MMBD4148	MMBD4448	UNITS
Maximum Recurrent Peak Reverse Voltage	Vrrm	100		V
Maximum Average Rectified Current	lo	150		mA
Peak Forward Surge Current IFM(surge): 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)	IFSM	2.0	4.0	A
Maximum Power Dissipation Tamb=25°C	Ptot	350		mW
Maximum Forward Voltage	VF	1.0 @ IF=10mA	0.72 @ IF=5mA	V
Maximum Reverse Current @VR=75V	lr	2.5		μΑ
Maximum Reverse Recovery Time(NOTE 1)	trr	4.0		nS
Typical Junction Capacitance(NOTE 2)	CJ	4.0		pF
Typical Thermal Resistance	RθJA	357		°C/W
Operating and Storage Temperature Range	TJ,TSTG	-55 to +125		°C

NOTE: 1. Test conditions: IF=IR=10mA, VR=6V, RL=100Ω, measured at IRR=1mA

2. Measured at 1.0MHz and VR=0

RATING AND CHARACTERISTIC CURVES (MMBD4148, MMBD4448)



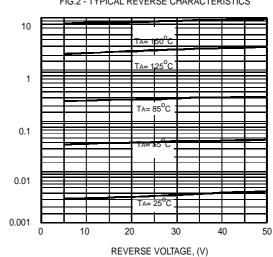


FIG.2 - TYPICAL REVERSE CHARACTERISTICS

FIG.3 - TYPICAL JUNCTION CAPACITANCE

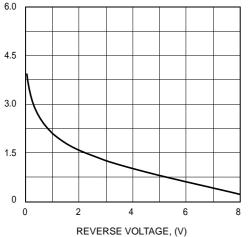


FIG.4 - RECTIFICATION EFFICIENCY MEASUREMENT CIRCUIT

